

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK2601

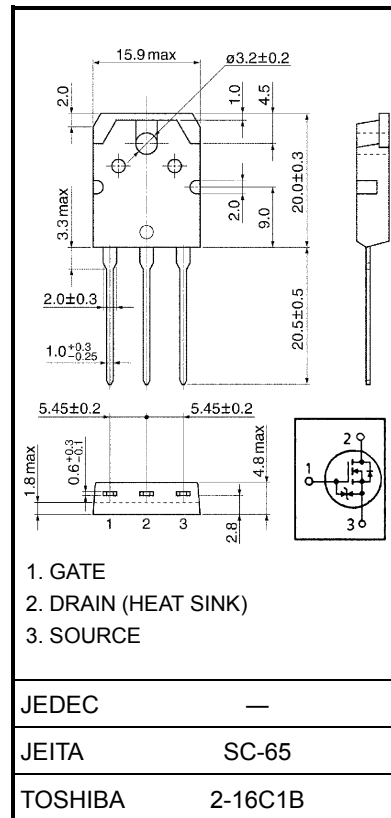
## DC-DC Converter, Relay Drive and Motor Drive Applications

Unit: mm

- Low drain-source ON resistance :  $R_{DS}(\text{ON}) = 0.75 \, \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 7.0 \, \text{S}$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \, \mu\text{A}$  (max) ( $V_{DS} = 500 \, \text{V}$ )
- Enhancement-mode :  $V_{th} = 2.0 \sim 4.0 \, \text{V}$  ( $V_{DS} = 10 \, \text{V}$ ,  $I_D = 1 \, \text{mA}$ )

### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	500	V
Drain-gate voltage ( $R_{GS} = 20\text{ k}\Omega$ )		$V_{DGR}$	500	V
Gate-source voltage		$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	10	A
	Pulse (Note 1)	$I_{DP}$	40	A
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )		$P_D$	125	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	270	mJ
Avalanche current		$I_{AR}$	10	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	12.5	mJ
Channel temperature		$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	$-55\sim 150$	$^\circ\text{C}$



Weight: 4.6 g (typ.)

## Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.0	$^{\circ}C / W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	50	$^{\circ}C / W$

Note 1: Please use devices on condition that the channel temperature is below 150°C.

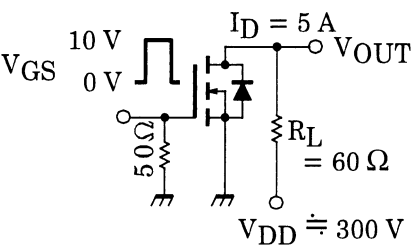
Note 2:  $V_{DD} = 90\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 4.59\text{ mH}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = 10\text{ A}$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.

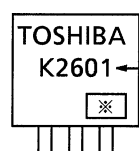
## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10 \mu\text{A}$ , $V_{DS} = 0 \text{ V}$	$\pm 30$	—	—	V
Drain cut-off current		$I_{DSS}$	$V_{DS} = 500 \text{ V}$ , $V_{GS} = 0 \text{ V}$	—	—	100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}$ , $V_{GS} = 0 \text{ V}$	500	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 5 \text{ A}$ ,	—	0.75	1.0	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}$ , $I_D = 5 \text{ A}$	3.5	7.0	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 10 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	—	1200	—	pF
Reverse transfer capacitance		$C_{rss}$		—	200	—	
Output capacitance		$C_{oss}$		—	550	—	
Switching time	Rise time	$t_r$		—	30	—	ns
	Turn-on time	$t_{on}$		—	50	—	
	Fall time	$t_f$		—	45	—	
	Turn-off time	$t_{off}$		—	180	—	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 400 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 10 \text{ A}$	—	30	—	nC
Gate-source charge		$Q_{gs}$		—	15	—	
Gate-drain ("miller") Charge		$Q_{gd}$		—	15	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	10	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	40	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 10 \text{ A}$ , $V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 10 \text{ A}$ , $V_{GS} = 0 \text{ V}$	—	1200	—	ns
Reverse recovery charge	$Q_{rr}$	$dI_{DR} / dt = 100 \text{ A} / \mu\text{s}$	—	10	—	$\mu\text{C}$

## Marking



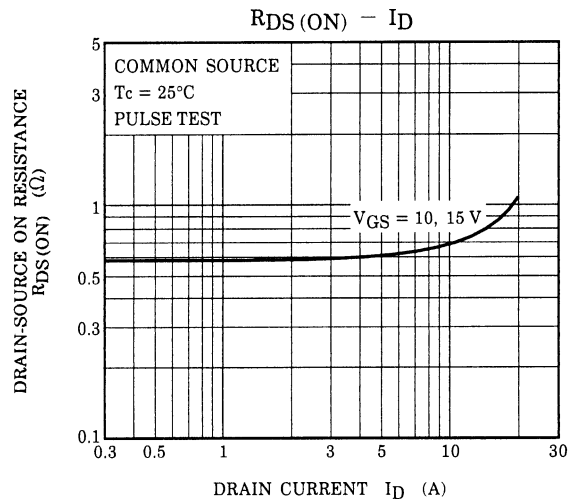
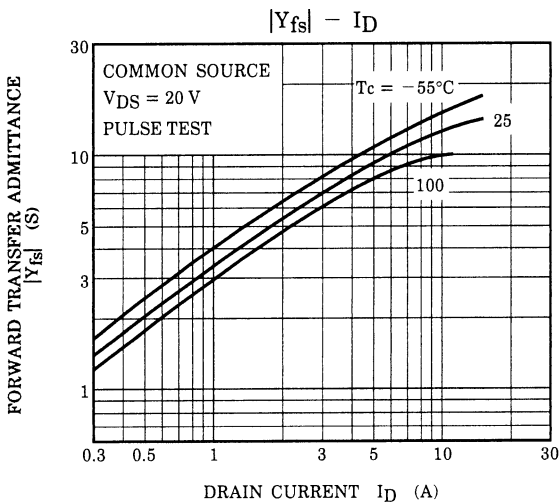
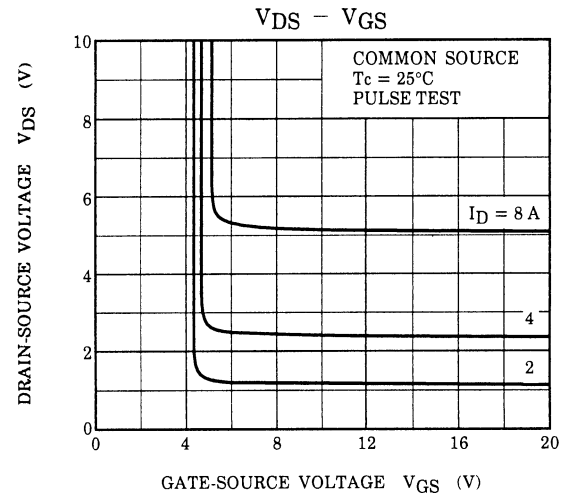
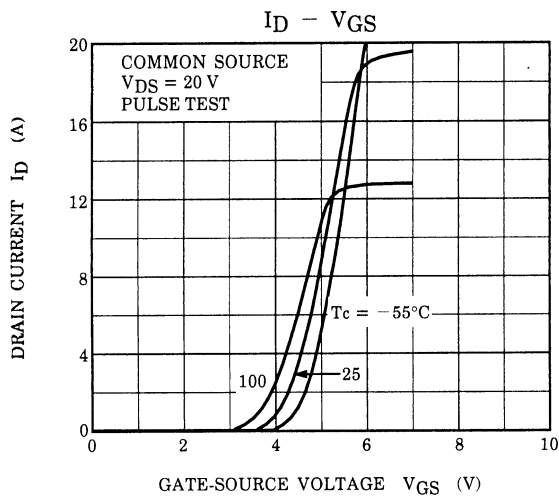
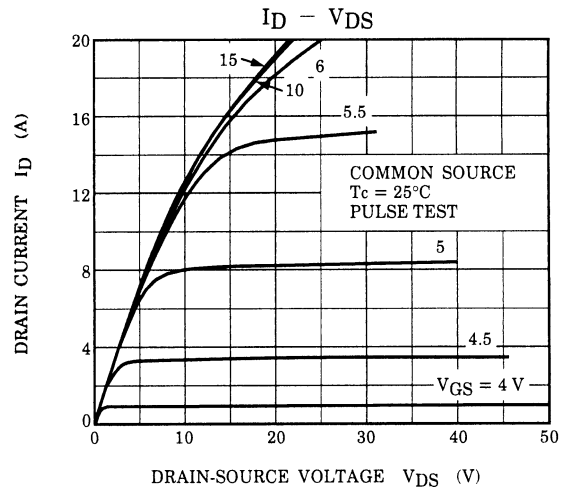
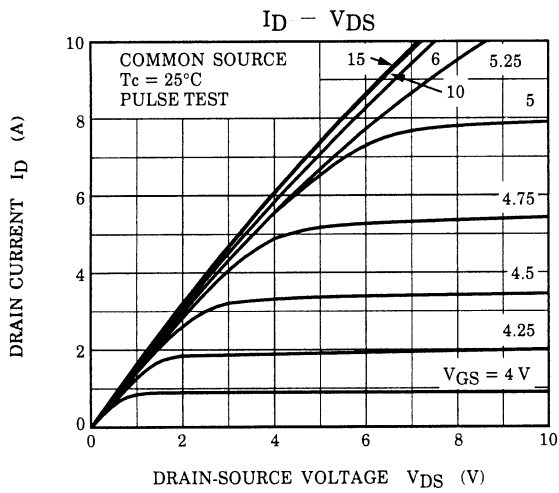
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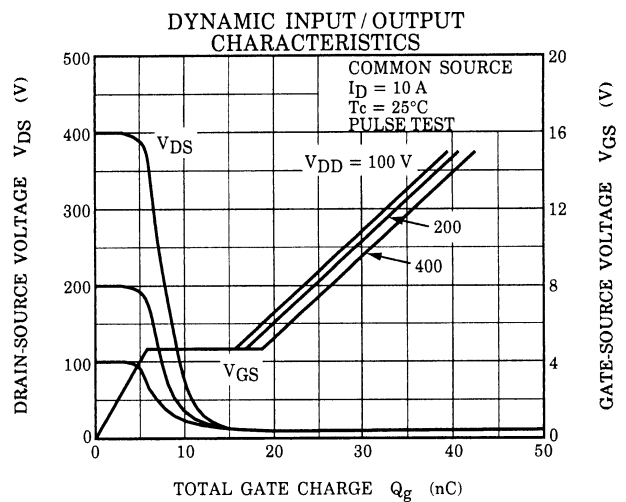
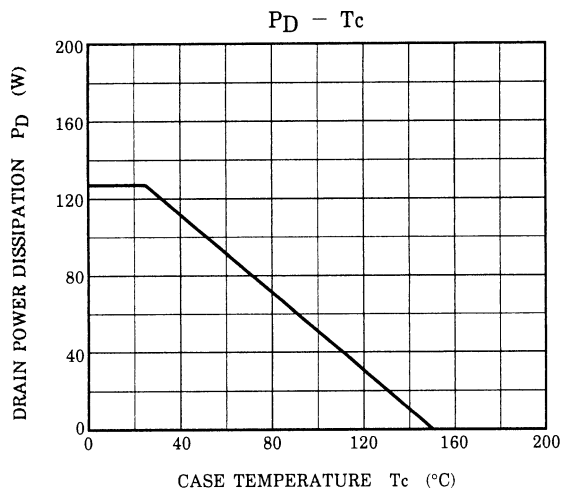
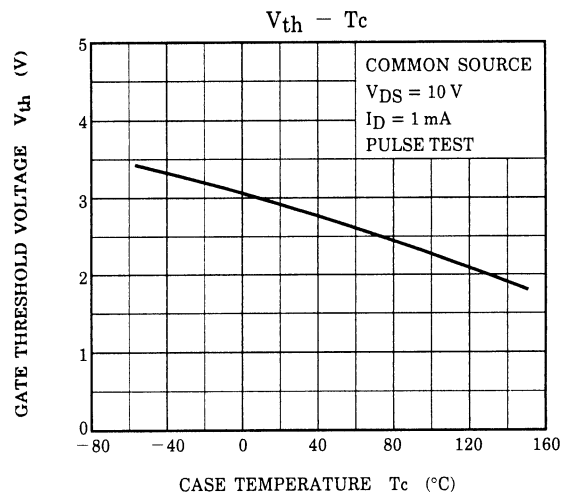
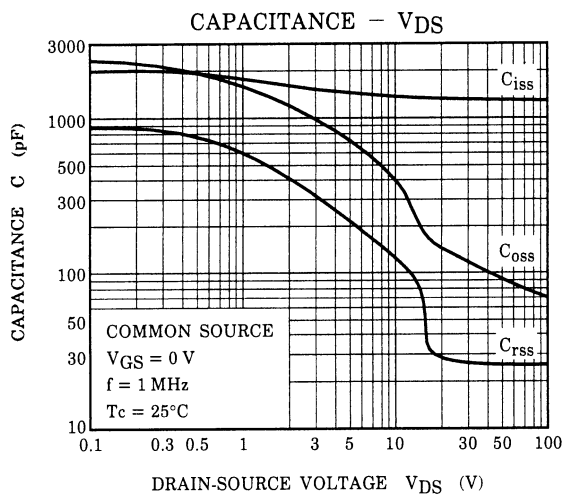
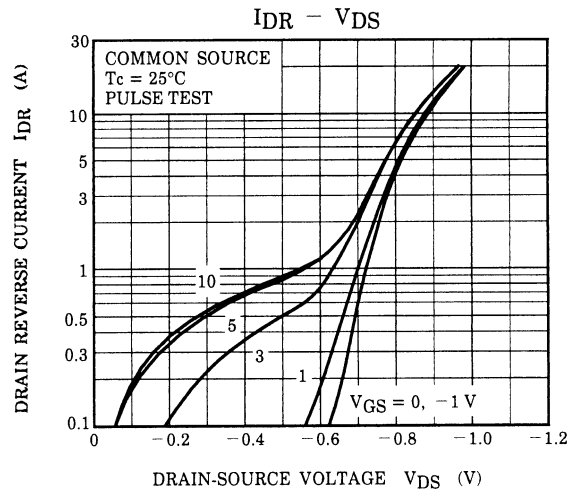
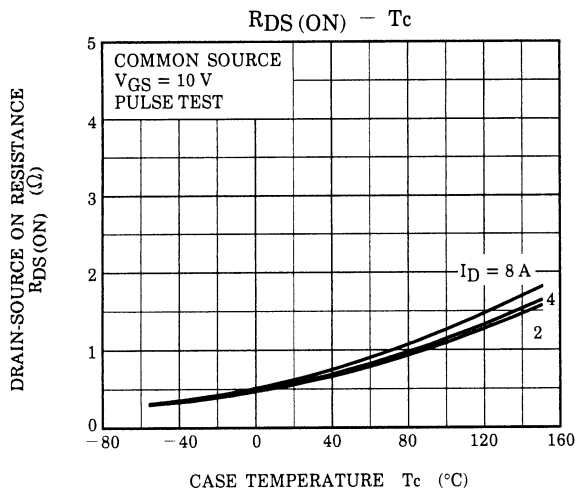
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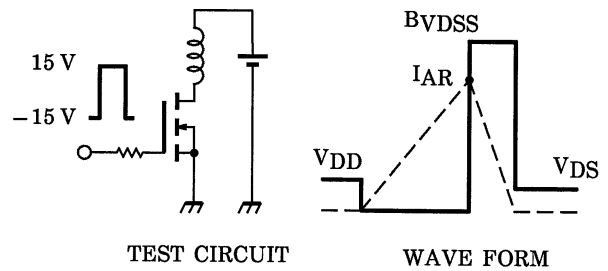
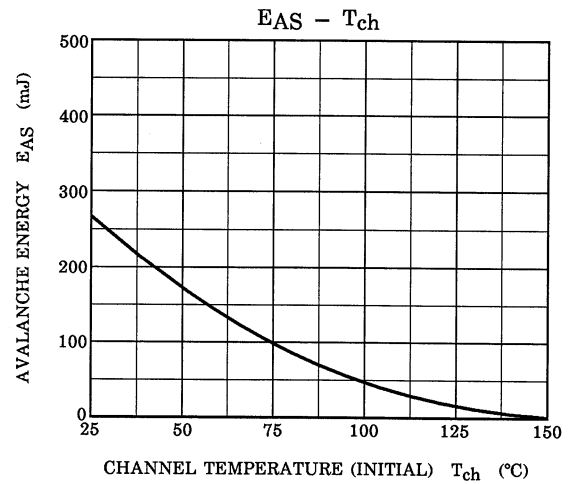
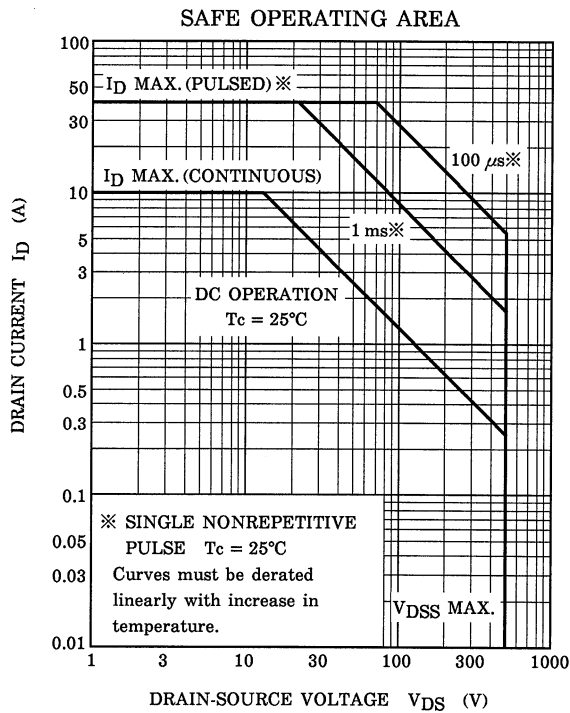
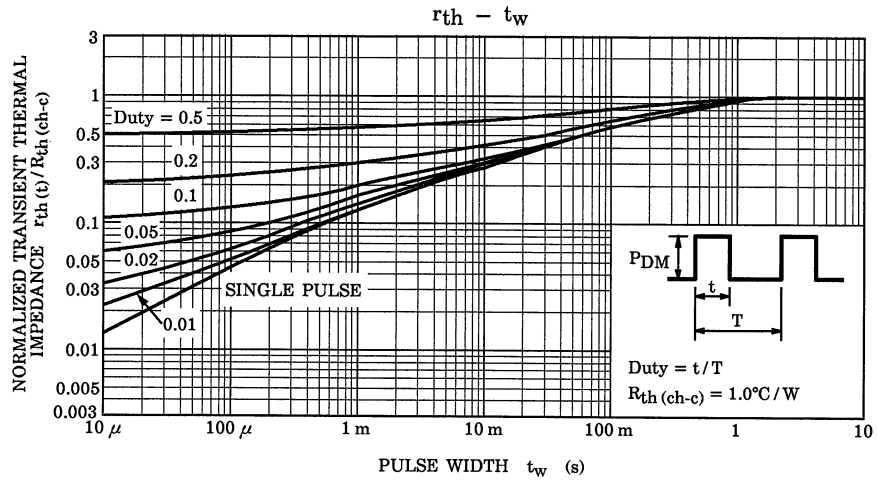


Month (Starting from Alphabet A)

Year (Last Number of the Christian Era)







$$R_G = 25 \, \Omega$$

$$V_{DD} = 90 \, \text{V}, L = 4.59 \, \text{mH}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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